Testing topological protection of edge states in bismuthene on SiC: New room-temperature quantum spin-Hall system

Fernando Dominguez, Benedikt Scharf, Gang Li, Werner Hanke, Ronny Thomale, and E. M. Hankiewicz Inst. for Theoretical Physics and Astrophysics, Univ. of Wurzburg, 97074 Wurzburg, Germany and School of Physical Science and Technology, ShanghaiTech University, Shanghai 201210, China

Due to its large bulk bandgap, bismuthene on SiC offers intriguing new opportunities for new roomtemperature quantum spin-Hall (QSH) applications. Although edge states have been observed in the local density of states (LDOS), to date there has been no experimental evidence that they are spin-polarized and topologically protected. We predict experimentally-testable fingerprints of these properties originating from magnetic fields, such as changes in the LDOS and in ballistic magnetotransport. In particular, for armchair edges we find a distinct difference of behavior under out-of-plane (gap opening of a few meV between the QSH states) and in-plane (no or tiny gap) fields. While we focus here on bismuthene on SiC, our main findings should also be applicable to other honeycomb-lattice-based QSH systems.